P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (mΩ)(Typ.)	I_D (A)[a]	Q_g (Typ.)
-30	13 at V_{GS} = -10 V	-8	40 nC
	22 at V_{GS} = -4.5 V		

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

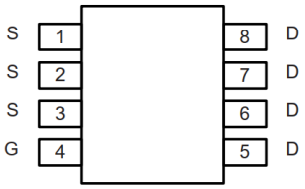
Pb-free

RoHS COMPLIANT

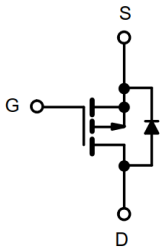
APPLICATIONS

- Adaptor Switch
- Notebook

SO-8



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C	I_D	- 8	A
	T_C = 125 °C		- 6.1	
Continuous Source Current (Diode Conduction)		I_S	- 6.2	
Pulsed Drain Current[a]		I_{DM}	- 32	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	- 25	
Single Pulse Avalanche Energy		E_{AS}	31	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	6.8	W
	T_C = 125 °C		2.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient[c,d]	PCB Mount[b]	R_{thJA}	85	°C/W
Junction-to-Foot (Drain)		R_{thJF}	22	

Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.
c. Maximum under steady state conditions is 100 °C/W
d. Based on T_C = 25 °C.

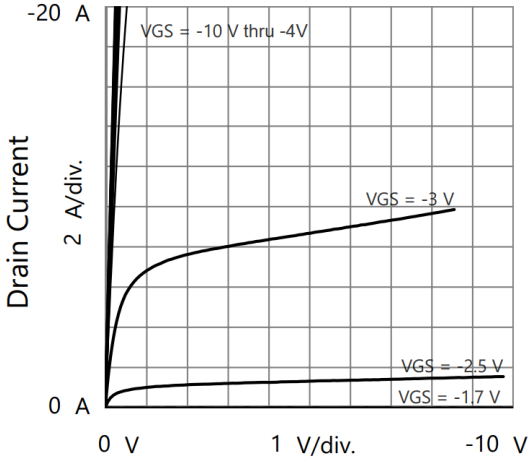
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = - 250 µA		- 30	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA		- 1	-	- 2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = -30 V		-	-	- 1	µA
		V_{GS} = 0 V, V_{DS} = -30 V , T_J = 125 °C		-	-	- 50	
		V_{GS} = 0 V, V_{DS} = -30 V , T_J = 175 °C		-	-	- 150	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = - 10 V, V_{DS} ≤ -5		- 8	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = -8 A		-	13	16	mΩ
		V_{GS} = - 10 V, I_D = -8 A, T_J = 125 °C		-	-	26	
		V_{GS} = - 10 V, I_D = -8 A, T_J = 175 °C		-	-	30	
		V_{GS} = - 4.5 V, I_D = -6 A		-	22	25	
Forward Transconductance[b]	g_{fs}	V_{DS} = - 15 V, I_D = - 8 A		-	20	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = - 15 V, f = 1 MHz	-	2360	-	pF
Output Capacitance	C_{oss}			-	260	-	
Reverse Transfer Capacitance	C_{rss}			-	260	-	
Total Gate Charge[c]	Q_g	V_{GS} = - 10 V	V_{DS} = - 15 V, I_D = - 8 A	-	40	-	nC
Gate-Source Charge[c]	Q_{gs}			-	6	-	
Gate-Drain Charge[c]	Q_{gd}			-	10	-	
Gate Resistance	R_g	f = 1 MHz		-	6	-	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 15 Ω I_D ≅ - 8 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	10	-	ns
Rise Time[c]	t_r			-	8	-	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	42	-	
Fall Time[c]	t_f			-	10	-	
Source-Drain Diode Ratings and Characteristics[b]							
Continous Source-Drain Diode Current	I_S	T_C = 25 °C		-	-	- 8	A
Pulse Diode Forward Current	I_{SM}			-	-	- 32	
Body Diode Voltage	V_{SD}	I_S = - 1 A, V_{GS} = 0 V		-	- 0.6	- 1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 8A, dI/dt = 100 A/µs, T_J = 25 °C		-	12	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	8	-	nC

Notes

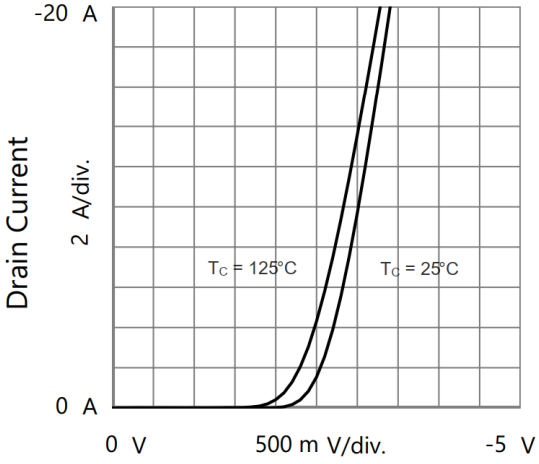
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

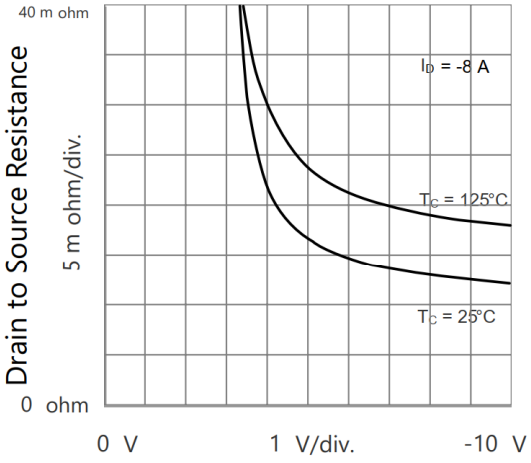
TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)



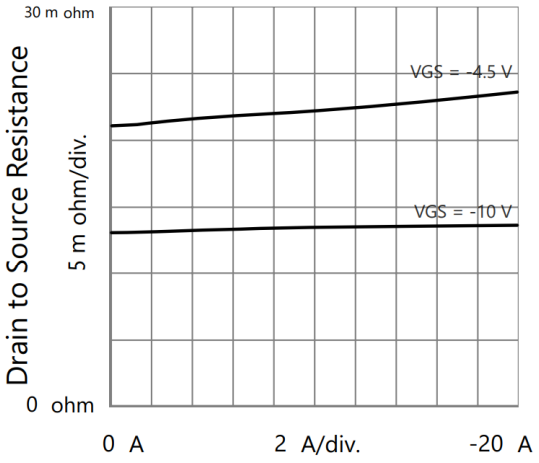
Drain to Source Voltage
Output Characteristics



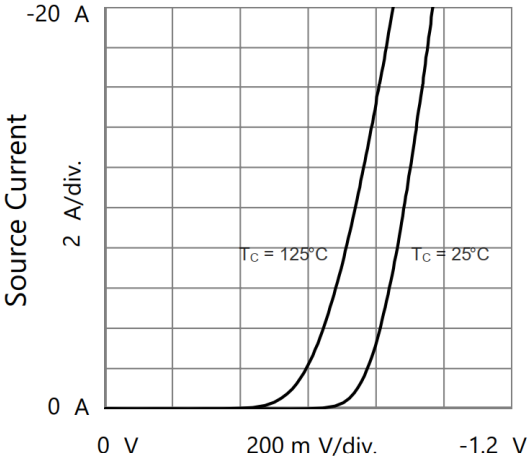
Gate to Source Voltage
Transfer Characteristics



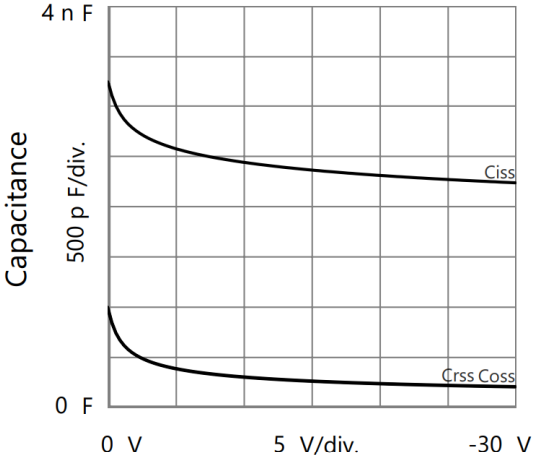
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

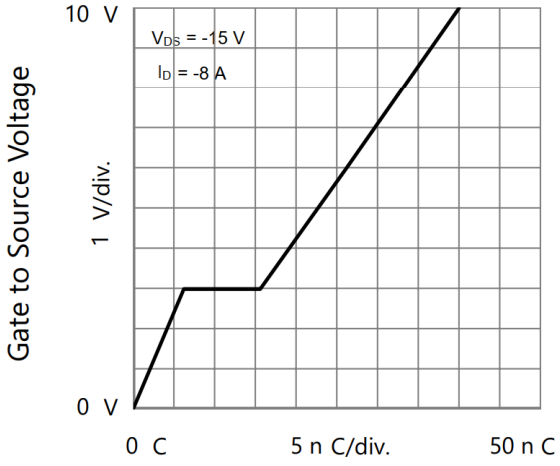


Source to Drain Voltage
Body Diode Forward Characteristics

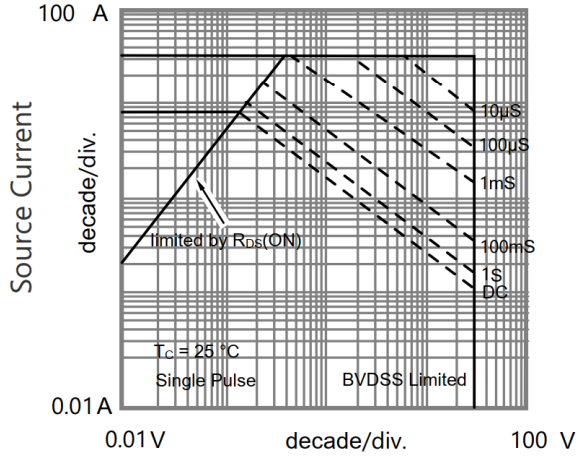


Drain to Source Voltage
Capacitances

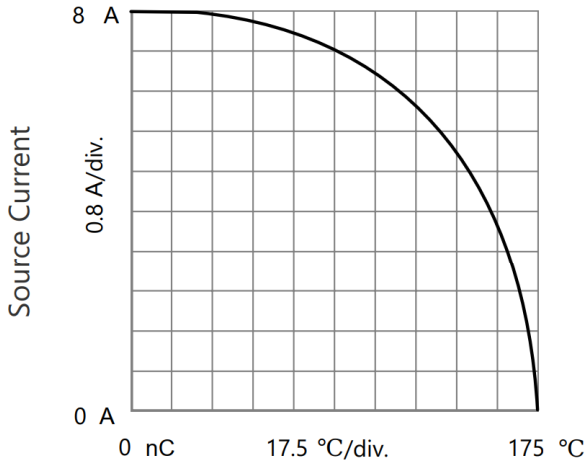
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



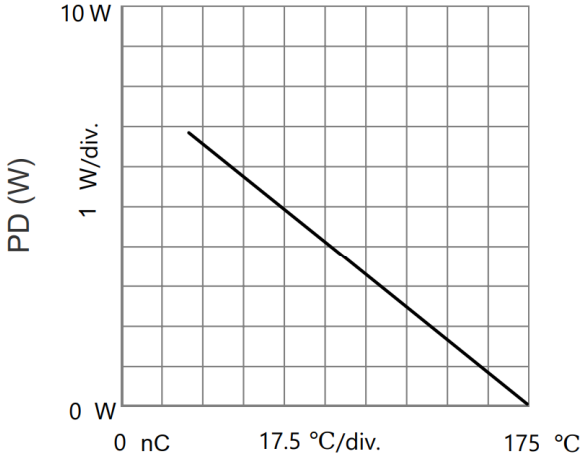
Gate to Source Voltage vs. GateCharge



Safe Operating Area, Junction-to-Ambient

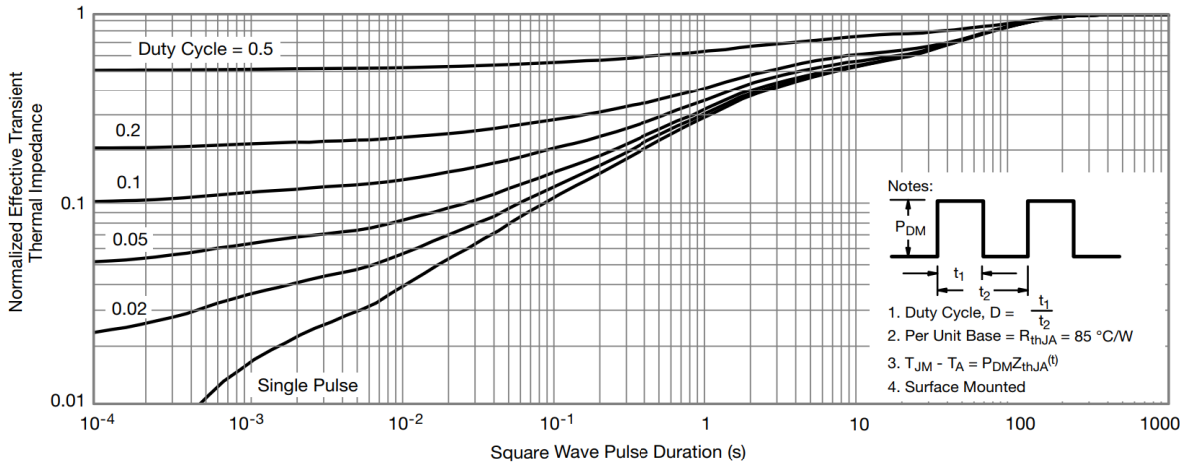


Current Derating

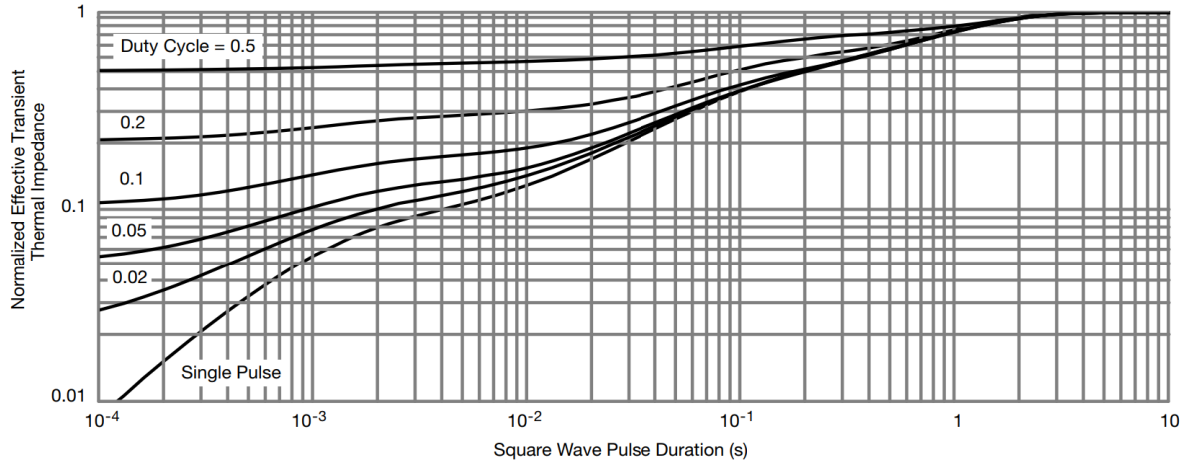


Power Derating

TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



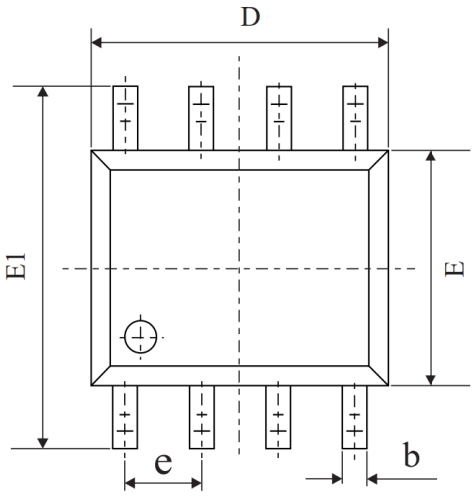
Normalized Thermal Transient Impedance, Junction-to-Foot

Note

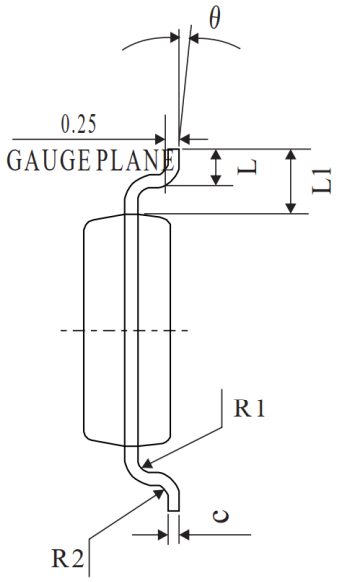
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

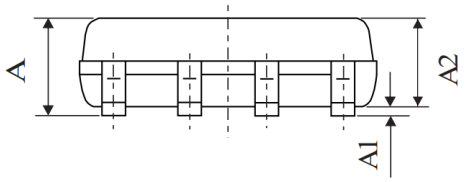
SOP-8 PACKAGE OUTLINE



TOP VIEW



SIDE VIEW



SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	1.30	1.60	1.85
A1	0.03	0.15	0.28
A2	1.20	1.45	1.70
b	0.26	0.40	0.54
C	0.132	0.203	0.273
D	4.50	4.90	5.30
E	3.50	3.00	4.30
E1	5.50	6.00	6.50
L	0.30	0.70	1.10
θ	2°	4°	6°
L1	1.04REF		
e	1.27BSC		
R1	0.07TYP		
R2	0.07TYP		

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